

# Marta Bagatin

## List of Publications by Year in descending order

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docs citations

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#	ARTICLE	IF	CITATIONS
1	TID Effects in Highly Scaled Gate-All-Around Si Nanowire CMOS Transistors Irradiated to Ultrahigh Doses. IEEE Transactions on Nuclear Science, 2022, 69, 1444-1452.	2.0	11
2	Energy Deposition by Ultrahigh Energy Ions in Large and Small Sensitive Volumes. IEEE Transactions on Nuclear Science, 2022, 69, 241-247.	2.0	1
3	Radiation Tolerant Multi-Bit Flip-Flop System With Embedded Timing Pre-Error Sensing. IEEE Journal of Solid-State Circuits, 2022, 57, 2878-2890.	5.4	6
4	Secondary Particles Generated by Protons in 3-D nand Flash Memories. IEEE Transactions on Nuclear Science, 2022, 69, 1461-1466.	2.0	1
5	First Tests of a New Facility for Device-Level, Board-Level and System-Level Neutron Irradiation of Microelectronics. IEEE Transactions on Emerging Topics in Computing, 2021, 9, 104-108.	4.6	15
6	Depth Dependence of Threshold Voltage Shift in 3-D Flash Memories Exposed to X-Rays. IEEE Transactions on Nuclear Science, 2021, 68, 659-664.	2.0	2
7	A Heavy-Ion Beam Monitor Based on 3-D NAND Flash Memories. IEEE Transactions on Nuclear Science, 2021, 68, 884-889.	2.0	5
8	A Heavy-Ion Detector Based on 3-D NAND Flash Memories. IEEE Transactions on Nuclear Science, 2020, 67, 154-160.	2.0	17
9	Thermal Neutron-Induced SEUs in the LHC Accelerator Environment. IEEE Transactions on Nuclear Science, 2020, 67, 1412-1420.	2.0	14
10	Characterizing High-Energy Ion Beams With PIPS Detectors. IEEE Transactions on Nuclear Science, 2020, 67, 1421-1427.	2.0	5
11	Low-Power, Subthreshold Reference Circuits for the Space Environment: Evaluated with $\hat{I}^3$ -rays, X-rays, Protons and Heavy Ions. Electronics (Switzerland), 2019, 8, 562.	3.1	9
12	Total Ionizing Dose Effects in 3-D NAND Flash Memories. IEEE Transactions on Nuclear Science, 2019, 66, 48-53.	2.0	29
13	Atmospheric Neutron Soft Errors in 3-D NAND Flash Memories. IEEE Transactions on Nuclear Science, 2019, 66, 1361-1367.	2.0	12
14	The Effect of Proton Irradiation in Suppressing Current Collapse in AlGaIn/GaN High-Electron-Mobility Transistors. IEEE Transactions on Electron Devices, 2019, 66, 372-377.	3.0	19
15	Effects of Heavy-Ion Irradiation on Vertical 3-D NAND Flash Memories. IEEE Transactions on Nuclear Science, 2018, 65, 318-325.	2.0	38
16	Atmospheric-Like Neutron Attenuation During Accelerated Neutron Testing With Multiple Printed Circuit Boards. IEEE Transactions on Nuclear Science, 2018, 65, 1830-1834.	2.0	8
17	Upsets in Erased Floating Gate Cells With High-Energy Protons. IEEE Transactions on Nuclear Science, 2017, 64, 421-426.	2.0	1
18	Single Event Upsets Induced by Direct Ionization from Low-Energy Protons in Floating Gate Cells. IEEE Transactions on Nuclear Science, 2017, 64, 464-470.	2.0	16

#	ARTICLE	IF	CITATIONS
19	Space Environment Effects on Flexible, Low-Voltage Organic Thin-Film Transistors. ACS Applied Materials & Interfaces, 2017, 9, 35150-35158.	8.0	18
20	Experimental and Simulation Study of the Effects of Heavy-ion Irradiation on HfO <sub>2</sub> -based RRAM Cells. IEEE Transactions on Nuclear Science, 2017, , 1-1.	2.0	11
21	A low cost robust radiation hardened flip-flop circuit. , 2017, , .		3
22	Simulation and Experiment in Neutron Induced Single Event Effects in SRAM. , 2017, , .		0
23	Single Event Transients and Pulse Quenching Effects in Bandgap Reference Topologies for Space Applications. IEEE Transactions on Nuclear Science, 2016, 63, 2950-2961.	2.0	15
24	Muon-induced soft errors in 16-nm NAND flash memories. , 2016, , .		2
25	Radiation Vulnerability in 65 nm CMOS I/O Transistors after Exposure to Grad Dose. , 2015, , .		1
26	Drain Current Collapse in 65Ånm pMOS Transistors After Exposure to Grad Dose. IEEE Transactions on Nuclear Science, 2015, 62, 2899-2905.	2.0	21
27	Proton Irradiation Effects on Commercial Laser Diodes. , 2015, , .		4
28	Sample-to-Sample Variability of Floating Gate Errors Due to Total Ionizing Dose. IEEE Transactions on Nuclear Science, 2015, 62, 2511-2516.	2.0	12
29	Sensitive Volume and Extreme Shifts in Floating Gate Cells Irradiated with Heavy Ions. IEEE Transactions on Nuclear Science, 2015, 62, 2815-2821.	2.0	5
30	Investigation of Hot Carrier Stress and Constant Voltage Stress in High- <math>\kappa</math> Si-Based TFETs. IEEE Transactions on Device and Materials Reliability, 2015, 15, 236-241.	2.0	14
31	Total Ionizing Dose Effects in Si-Based Tunnel FETs. IEEE Transactions on Nuclear Science, 2014, 61, 2874-2880.	2.0	15
32	Degradation of dc and pulsed characteristics of InAlN/GaN HEMTs under different proton fluences. , 2014, , .		2
33	Recoverable degradation of blue InGaN-based light emitting diodes submitted to 3â€‰%MeV proton irradiation. Applied Physics Letters, 2014, 105, 213506.	3.3	10
34	Upsets in Phase Change Memories Due to High-LET Heavy Ions Impinging at an Angle. IEEE Transactions on Nuclear Science, 2014, 61, 3491-3496.	2.0	8
35	Sample-to-Sample Variability and Bit Errors Induced by Total Dose in Advanced NAND Flash Memories. IEEE Transactions on Nuclear Science, 2014, 61, 2889-2895.	2.0	23
36	Neutron and Alpha Single Event Upsets in Advanced NAND Flash Memories. IEEE Transactions on Nuclear Science, 2014, 61, 1799-1805.	2.0	13

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37	Analysis of TID Failure Modes in SRAM-Based FPGA Under Gamma-Ray and Focused Synchrotron X-Ray Irradiation. IEEE Transactions on Nuclear Science, 2014, 61, 1777-1784.	2.0	15
38	Effects of bias on the radiation responses of Si-based TFETs. , 2014, , .		1
39	Radiation Effects in Flash Memories. IEEE Transactions on Nuclear Science, 2013, 60, 1953-1969.	2.0	116
40	Single and Multiple Cell Upsets in 25-nm NAND Flash Memories. IEEE Transactions on Nuclear Science, 2013, 60, 2675-2681.	2.0	24
41	Degradation of Sub 40-nm NAND Flash Memories Under Total Dose Irradiation. IEEE Transactions on Nuclear Science, 2012, 59, 2952-2958.	2.0	21
42	Alpha-induced soft errors in Floating Gate flash memories. , 2012, , .		8
43	Retention Errors in 65-nm Floating Gate Cells After Exposure to Heavy Ions. IEEE Transactions on Nuclear Science, 2012, 59, 2785-2790.	2.0	12
44	Effects of Total Ionizing Dose on the Retention of 41-nm NAND Flash Cells. IEEE Transactions on Nuclear Science, 2011, 58, 2824-2829.	2.0	19
45	Impact of Technology Scaling on the Heavy-Ion Upset Cross Section of Multi-Level Floating Gate Cells. IEEE Transactions on Nuclear Science, 2011, 58, 969-974.	2.0	37
46	Angular Dependence of Heavy-Ion Induced Errors in Floating Gate Memories. IEEE Transactions on Nuclear Science, 2011, 58, 2621-2627.	2.0	23
47	A study on the short- and long-term effects of X-ray exposure on NAND Flash memories. , 2011, , .		8
48	Heavy-Ion Induced Threshold Voltage Tails in Floating Gate Arrays. IEEE Transactions on Nuclear Science, 2010, , .	2.0	37
49	Increase in the Heavy-Ion Upset Cross Section of Floating Gate Cells Previously Exposed to TID. IEEE Transactions on Nuclear Science, 2010, , .	2.0	28
50	Catastrophic Failure in Highly Scaled Commercial NAND Flash Memories. IEEE Transactions on Nuclear Science, 2010, 57, 266-271.	2.0	37
51	Scaling trends of neutron effects in MLC NAND Flash memories. , 2010, , .		11
52	A multi-megarad, radiation hardened by design 512 kbit SRAM in CMOS technology. , 2010, , .		6